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(54) Title: WAFER, ROUGHNESS IMPROVEMENT METHOD AND APPARATUS THEREFOR, DEVICE, AND MEDIUM

(54) 发明名称: 晶圆及其粗糙度的改善方法、装置、设备及介质

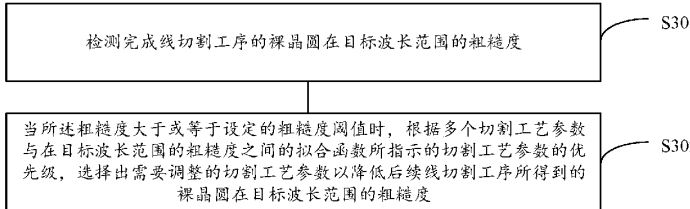


图 3

- S301 Detect a roughness of a bare wafer in a target wavelength range after a line cutting process is completed
- S302 When the roughness is greater than or equal to a set roughness threshold, then, based on priorities of multiple cutting process parameters and cutting process parameters indicated by a fitting function between the multiple cutting process parameters and the roughness in the target wavelength range, select cutting process parameters that need to be adjusted to reduce the roughness of the bare wafer in the target wavelength range obtained during a subsequent line cutting process

(57) Abstract: The present disclosure provides a wafer, a roughness improvement method and apparatus therefor, a device, and a medium. The method comprises: detecting a roughness of a bare wafer in a target wavelength range after a line cutting process is completed; when the roughness is greater than or equal to a set roughness threshold, then, based on priorities of multiple cutting process parameters and cutting process parameters indicated by a fitting function between the multiple cutting process parameters and the roughness in the target wavelength range, selecting cutting process parameters that need to be adjusted so as to reduce the roughness of the bare wafer in the target wavelength range obtained during a subsequent line cutting process.

(57) 摘要: 本公开提供了一种晶圆及其粗糙度的改善方法、装置、设备及介质; 该方法包括: 检测完成线切割工序的裸晶圆在目标波长范围的粗糙度; 当所述粗糙度大于或等于设定的粗糙度阈值时, 根据多个切割工艺参数与在目标波长范围的粗糙度之间的拟合函数所指示的切割工艺参数的优先级, 选择出需要调整的切割工艺参数以降低后续线切割工序所得到的裸晶圆在目标波长范围的粗糙度。

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— 包括国际检索报告(条约第21条(3))。